



40V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > 40V
- I_C = 5A High Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < 120mV @ 1A
- R_{SAT} = 50mΩ @ 5A for a Low Equivalent On-Resistance
- hFE Specified up to 10A for a High Gain Hold-Up
- Complementary PNP Type: FZT1151A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
 A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

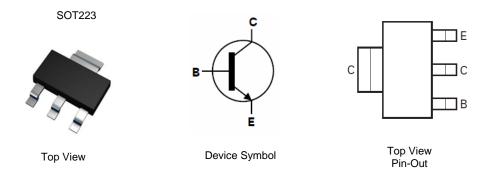
https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 [®]
- Weight: 0.112 grams (Approximate)

Applications

- Solenoid, Relay and Actuator Drivers
- DC Modules
- Motor Control



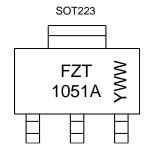
Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT1051ATA	AEC-Q101	FZT1051A	7	12	1,000
FZT1051ATC	AEC-Q101	FZT1051A	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



FZT 1051A = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 9 = 2019) WW or $\overline{W}W$ = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	VCEO	40	V
Emitter-Base Voltage	VEBO	7	V
Continuous Collector Current	lc	5	Α
Peak Pulse Current	Ісм	20	Α
Base Current	lΒ	1	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0	W	
Power Dissipation	(Note 6)	Po	2.0		
Power Dissipation	(Note 7)	PD	1.6	VV	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	D	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		Rejl	10.9		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 10)

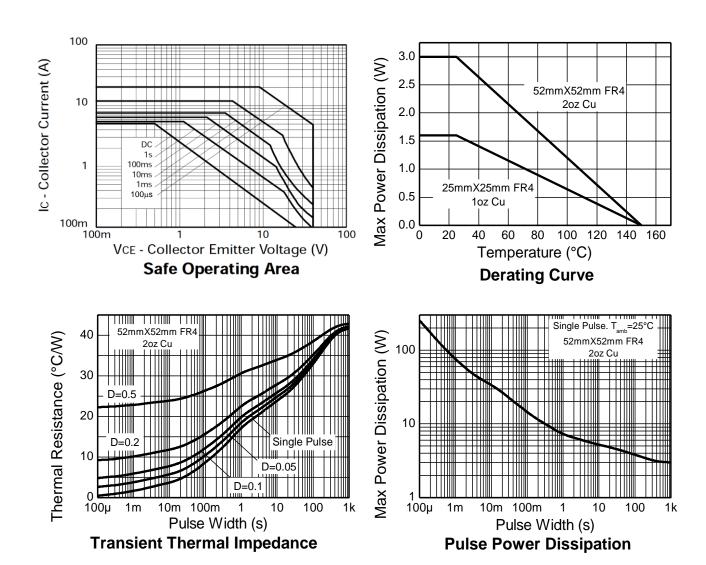
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

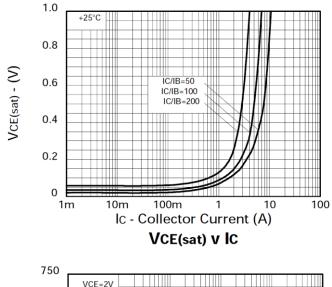
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	190	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BVces	150	190	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	BVcev	150	190	_	V	Ic = 100μA, V _{EB} = 1V
Collector-Emitter Breakdown Voltage (Note 11)	BVceo	40	60	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BVEBO	7	8.1	_	V	I _E = 100μA
Collector Cut-Off Current	I _{CBO}	_	<1 —	10 0.5	nΑ μΑ	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Collector Cut-Off Current	I _{CES}	_	<1	10	nA	V _{CB} = 120V
Emitter Cut-Off Current	I _{ЕВО}	_	<1	10	nA	VEB = 6V
	VCE(sat)	_	17	25	mV	Ic = 200mA, I _B = 10mA
Collector Emitter Seturation Voltage (Note 11)		_	85	120		$I_C = 1A$, $I_B = 10mA$
Collector-Emitter Saturation Voltage (Note 11)		_	140	180		$I_C = 2A$, $I_B = 20mA$
		_	250	340		$I_C = 5A$, $I_B = 100mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE} (sat)	_	980	1100	mV	Ic = 5A, I _B = 100mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	915	1000	mV	Ic = 5A, VcE = 2V
		290	440	_		$I_C = 10mA$, $V_{CE} = 2V$
DC Current Coin (Note 11)	hFE	270	450	1200		Ic = 1A, VcE = 2V
DC Current Gain (Note 11)		130	220	_	_	Ic = 5A, VcE = 2V
		40	55	_		$I_C = 10A, V_{CE} = 2V$
Output Capacitance	Cobo	_	27	40	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	fτ	_	155	_	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Switching Times	ton	_	220	_	ns	Ic = 3A, $Vcc = 10V$,
Switching Times	t _{off}	_	540	_	115	$I_{B1} = -I_{B2} = 30 \text{mA}$

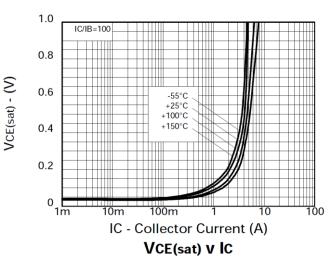
Note:

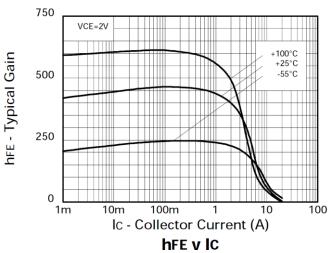
11. Measured under pulsed conditions. Pulse width $\leq 300 \mu s.$ Duty cycle $\leq 2\%$

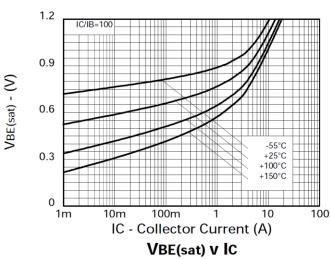


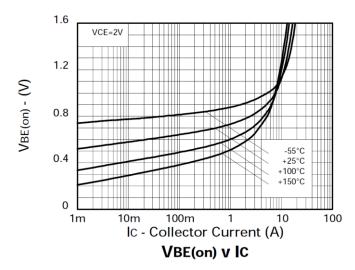
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









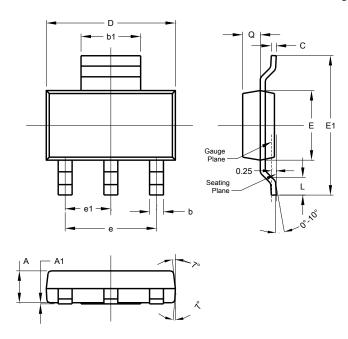




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

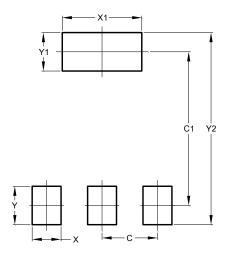


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8 00



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